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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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| Application Number | |
| Filing Date | |
| First Named Inventor | Chan Woo Park |
| Art Unit | |
| Examiner Name | |
| Attorney Docket Number | 51876P386 |

**NON PATENT LITERATURE DOCUMENTS**

| Examiner Initials* | Cite No.[1] | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T[2] |
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| Examiner Signature | T. Nguyen | Date Considered | 8/16/05 |
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| Complete if Known | |
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| Application Number | 10/677,665 |
| Filing Date | October 1, 2003 |
| First Named Inventor | Chan Woo Park |
| Art Unit | 2813 |
| Examiner Name | NGUYEN, TUAN |
| Attorney Docket Number | 51876P386 |

## U.S. PATENT DOCUMENTS

| Examiner Initials* | Cite No.[1] | Document Number: Number - Kind Code[2] *(if known)* | Publication Date or Issue Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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## FOREIGN PATENT DOCUMENTS

| Examiner Initials* | Cite No.[1] | Foreign Patent Document: Country Code[3] - Number[4] - Kind Code[5] *(if known)* | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T[6] |
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| Examiner Signature | T. NGUYEN | Date Considered | 8/16/05 |
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Sheet 1 of 1

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| Application Number | 10/677,665 |
| Filing Date | 10-1-03 |
| First Named Inventor | Chan Woo Park |
| Art Unit | 2813 |
| Examiner Name | |
| Attorney Docket Number | 51876P386 |

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| Examiner Signature | T. Nguyen | Date Considered | 8/16/05 |
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